

### **Description**

The RTE002P02 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

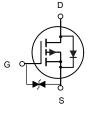


**SOT-523** 

#### **General Features**

 $V_{DS} = -20V I_{D} = -0.66A$ 

$$\begin{split} R_{DS(ON)} < 560 &\,\mathrm{m}\Omega @~V_{GS} \text{=-}4.5V \\ R_{DS(ON)} < 780 &\,\mathrm{m}\Omega @~V_{GS} \text{=-}2.5V \\ ESD &~Rating:~1500V HBM \end{split}$$



### **Application**

Battery protection

Load switch

Uninterruptible power supply

P-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
RTE002P02	SOT-523	HXY MOSFET	3000

### Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Parameter	Limit	Unit	
Drain-Source Voltage	-20	V	
Gate-Source Voltage	±12	V	
Drain Current-Continuous	-0.66	А	
Maximum Power Dissipation	150	mW	
Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$	
Thermal Resistance,Junction-to-Ambient (Note 2)	833	°C/W	
	Drain-Source Voltage  Gate-Source Voltage  Drain Current-Continuous  Maximum Power Dissipation  Operating Junction and Storage Temperature Range	Drain-Source Voltage -20  Gate-Source Voltage ±12  Drain Current-Continuous -0.66  Maximum Power Dissipation 150  Operating Junction and Storage Temperature Range -55 To 150	



# Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)

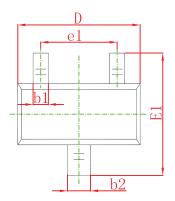
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit		
STATIC CHARACTERISTICE								
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =-250μA	-20			V		
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V,V <sub>GS</sub> = 0V			-1	μA		
Gate-body leakage current	Igss	V <sub>GS</sub> =±10V, V <sub>DS</sub> = 0V			±10	μA		
Gate threshold voltage (note2)	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.4	-0.7	-1.0	V		
	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-0.5A			0.56	Ω		
Drain-source on-resistance (note2)		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-0.2A			0.78	Ω		
Maximum Continuous Drain to Source Diode Forward Current	Is				-0.6	А		
Maximum Pulsed Drain to Source Diode Forward Current	Ism				-1.2	А		
Diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> =-0.5A, V <sub>GS</sub> = 0V			-1.2	V		
DYNAMIC CHARACTERISTICS (note4)								
Input capacitance	C <sub>iss</sub>			115		pF		
Output capacitance	Coss	V <sub>DS</sub> =-16V,V <sub>GS</sub> =0V, f =1MHz		15		pF		
Reverse transfer capacitance	C <sub>rss</sub>	1 - 1141112		9		pF		
SWITCHING CHARACTERISTICS (no	te4)				•	•		
Turn-on delay time (note3)	t <sub>d(on)</sub>			9		nS		
Turn-on rise time (note3)	t <sub>r</sub>	V <sub>GS</sub> =-4.5V,V <sub>DS</sub> =-10V,		6		nS		
Turn-off delay time (note3)	t <sub>d(off)</sub>	$I_D$ =-200mA, $R_{GEN}$ =10 $\Omega$		33		nS		
Turn-off fall time (note3)	t <sub>f</sub>			22		nS		

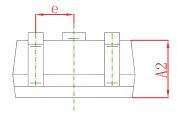
#### Notes:

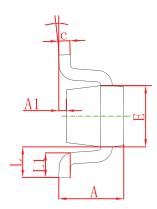
- 1. Surface mounted on FR4 board using the minimum recommended pad size.
- 2. Pulse Test : Pulse Width=300 $\mu$ s, Duty Cycle=2%.
- 3. Switching characteristics are independent of operating junction temperatures.
- 4. Guaranteed by design, not subject to producting.



# **SOT-523 Package Information**

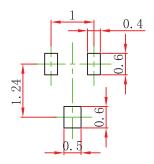






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	0.700	0.900	0.028	0.035	
A1	0.000	0.100	0.000	0.004	
A2	0.700	0.800	0.028	0.031	
b1	0.150	0.250	0.006	0.010	
b2	0.250	0.350	0.010	0.014	
С	0.100	0.200	0.004	0.008	
D	1.500	1.700	0.059	0.067	
Е	0.700	0.900	0.028	0.035	
E1	1.450	1.750	0.057	0.069	
е	0.500 TYP.		0.020 TYP.		
e1	0.900	1.100	0.035	0.043	
L	0.400 REF.		0.016 REF.		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

# **SOT-523 Suggested Pad Layout**



#### Note:

- 1. Controlling dimension: in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.



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